



PRODUCT BULLETIN # 20205Generic Copy

Issue Date: 27-Aug-2013**TITLE:** LMV358DMR2G Bond Pad structure change**PROPOSED FIRST SHIP DATE:** 27-Nov-2013**AFFECTED CHANGE CATEGORY(S):** Device Ordering Code**FOR ANY QUESTIONS CONCERNING THIS NOTIFICATION:**Contact your local ON Semiconductor sales office or <Shannon.riggs@onsemi.com>**NOTIFICATION TYPE:**ON Semiconductor considers this change approved unless specific conditions of acceptance are provided in writing. To do so, contact <quality@onsemi.com>.**DESCRIPTION AND PURPOSE:**

This product bulletin is to announce the completion of the qualification of the bond pad structure change on LMV358DMR2G. The change in bond pad structure is diagrammed below, and was determined necessary in order to eliminate the risk of bond pad damage during wire bond, and is the resulting action of EFAR 424841.

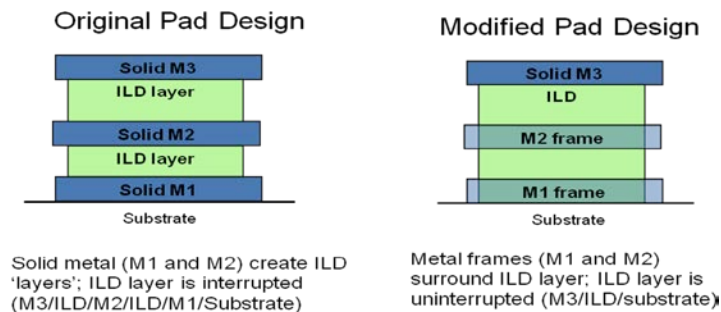


Figure 1: Cross Section representation of bond pad stack.
Original design (left), modified design (right).

There are no changes to the product datasheet as a result of the change in bond pad structure (http://www.onsemi.com/pub_link/Collateral/LMV321-LMV358-LMV324-D.PDF). The new pad structure has successfully passed the required reliability testing and has been released for production manufacturing as of April 2013.

**PRODUCT BULLETIN #20205****Qualification Results and Analysis:**

#	Test	Name	Test Conditions	End Point Req's	Test Results (rej/ss)				
					Read Point	Lot A	Lot B	Lot C	Lot 2
1	AC-PC	Precon Autoclave	TAmin = 121, RH = 100%, Pressure = 15 psig	c = 0, Room (96)	96h	0/77	0/77	0/77	0/77
7	TC+PC	Temperature Cycling	TAmin = -65C, TAmax = 150C	c = 0, Room (1000)	200	0/77	0/77	0/77	0/77
					500	0/77	0/77	0/77	0/77

Table 1: Qualification results for bond pad stack change.

List of affected General Parts:

LMV358DMR2G